650V/ 3A Silicon Carbide Power Schottky Barrier Diode

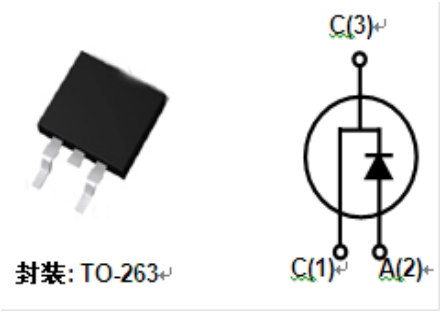
Features

- Rated to 650V at 3 Amps
- Zero reverse recovery current
- Zero forward recovery voltage
- Temperature independent switching behaviour
- High temperature operation
- High frequency operation

Key Characteristics		
V_{RRM}	650	V
I_F, $T_c \leqslant 155℃$	3	A
Q_C	11	nC

Benefits

- Unipolar rectifier
- Substantially reduced switching losses
- No thermal run-away with parallel devices
- Reduced heat sink requirements



Applications

- SMPS, e.g., CCM PFC;
- Motor drives, Solar application, UPS, Wind turbine, Rail traction, EV/HEV

Part No.	Package Type	Marking
G3S06503D	TO-263	G3S06503D

Maximum Ratings

Parameter	Symbol	Test Condition	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		650	V
Surge Peak Reverse Voltage	V_{RSM}		650	
DC Blocking Voltage	V_{DC}		650	
Continuous Forward Current	I_F	T_C=25℃ T_C=125℃ T_C=155℃	11.5 6.3 3	A
Repetitive Peak Forward Surge Current	I_{FRM}	T_C=25℃, tp=10ms，Half Sine Wave，D=0.3	15	A
Non-repetitive Peak Forward Surge Current	I_{FSM}	T_C=25℃, tp=10ms，Half Sine Wave	35	A
Power Dissipation	P_{TOT}	T_C=25℃	49	W
		T_C=110℃	21	W
Operating Junction	T_j		-55℃ to 175℃	℃
Storage Temperature	T_{stg}		-55℃ to 175℃	℃
Mounting Torque		M3 Screw 6-32 Screw	1 8.8	Nm lbf-in

Thermal Characteristics

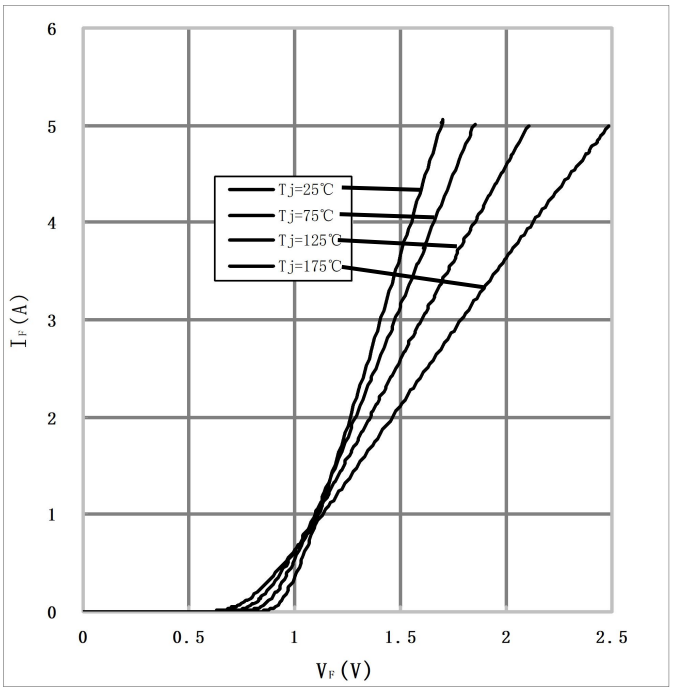
Parameter	Symbol	Test Condition	Value	Unit
			Typ.	
Thermal resistance from junction to case	$R_{th\ JC}$		3.07	℃/W

Electrical Characteristics

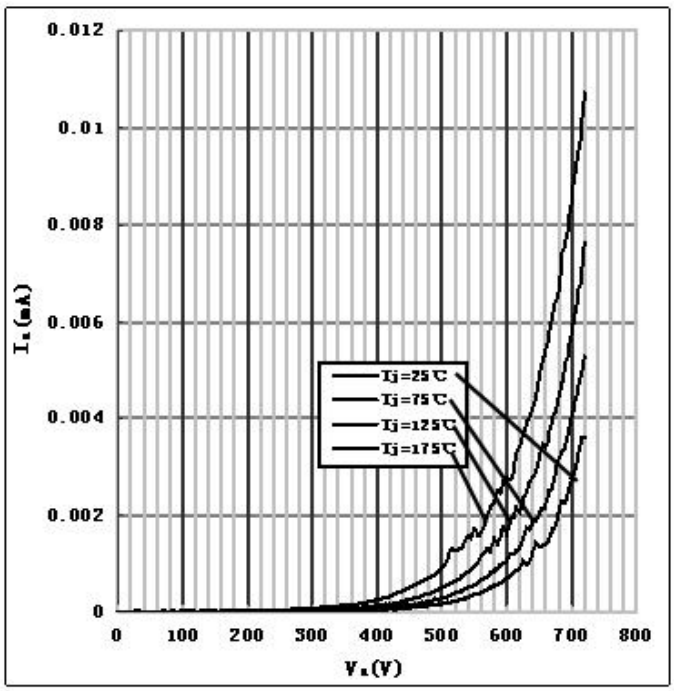
Parameter	Symbol	Test Conditions	Numerical		Unit
			Typ.	Max.	
Forward Voltage	V_F	I_F=3A, T_j=25℃	1.4	1.7	V
		I_F=3A, T_j=175℃	1.8	2.5	
Reverse Current	I_R	V_R=650V, T_j=25℃	10	50	μA
		V_R=650V, T_j=175℃	20	100	
Total Capacitive Charge	Q_C	V_R=400V, T_j=150℃ $Qc = \int_0^{VR} C(V)dV$	11	-	nC
Total Capacitance	C	V_R=0V, T_j=25℃, f=1MHZ	181	220	pF
		V_R=200V, T_j=25℃, f=1MHZ	22.5	25	
		V_R=400V, T_j=25℃, f=1MHZ	20.5	21	

Performance Graphs

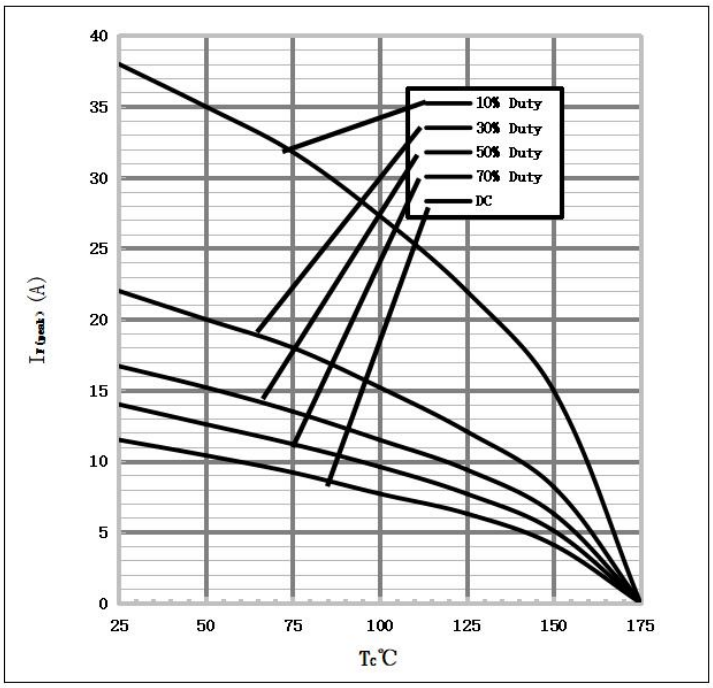
1) Forward IV characteristics as a function of Tj :



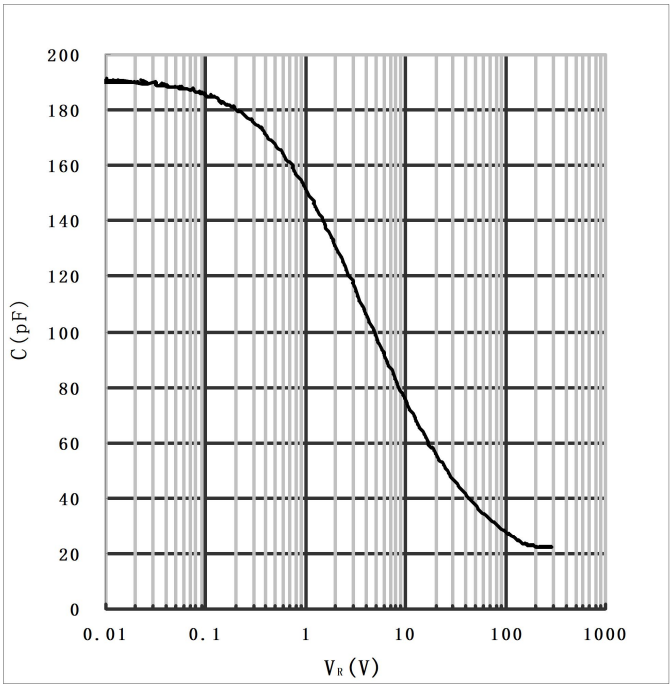
2) Reverse IV characteristics as a function of Tj :



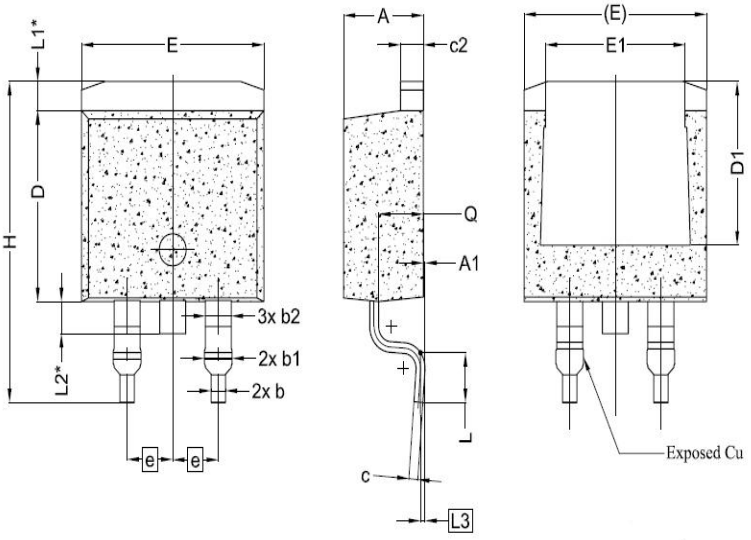
3)Current Derating



4)Capacitance vs. reverse voltage :



Package TO-263



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.70	0.80	0.90
b1	1.20	1.55	1.75
b2	1.20	1.45	1.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	—
E	9.96	10.16	10.36
E1	6.89	7.77	7.89
e	2.54 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L2	1.50 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70

Note: The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC(RoHS2). RoHS Certification and other certifications can be obtained from GPT sales representatives or GPT website: http://globalpowertech.cn/English/index.asp

More product datasheets and company information can be found in:
http://globalpowertech.cn/English/index.asp